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Sheet 1 of 1

<p>(Rev. 5/92) Comparable to Form PTO-1449</p> <p>U.S. Department of Commerce Patent and Trademark Office</p> <p>INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)</p>				Atty. Docket No. 82821		Serial No. 09/856,212		
				Applicant NAKAMURA et al.				
				Filing Date May 18, 2001		Group 1765		
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
MS		4,437,922	03/20/1984	Bischoff et al.	—	—	—	
MS		4,944,834	07/31/1990	Tada et al.	—	—	—	
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FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Name of Patentee	Class	Subclass	Translation Yes No	
MS		EP 0823497	02/11/1998	MEMC Electronic Materials, Inc.	—	—	X	
MS		EP 0866150	09/23/1998	Wacker Siltronic Gesellschaft fur	—	—	X	
		EP 0785298	06/26/2002	MEMC Electronic Materials, Inc.	—	—	X	
		JP 03-279290	12/10/1991	Osaka Titanium Co., Ltd.	—	—	X	
		JP 05-194076	08/03/1993	Komatsu Denshi Kinzoku KK	—	—	X	
		JP 07-133187	05/23/1995	Komatsu Electron Metals Co., Ltd.	—	—	X	
		WO 98/45507	10/15/1998	MEMC Electronic Materials, Inc.	—	—	X	
MS		WO 98/45508	10/15/1998	MEMC Electronic Materials, Inc.	—	—	X	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)								
MS		NAKAMURA, KOZO et al.: "Formation process of grown-in defects in Czochralski grown silicon crystals" JOURNAL OF CRYSTAL GROWTH 180 (1997) 61-72						
MS		AMMON, WILFRIED VON et al.: "The dependence of bulk defects on the axial temperature gradient of silicon crystals during Czochralski growth" 2300 JOURNAL OF CRYSTAL GROWTH 151 (1995) June 1, Nos. 3/4, Amsterdam, NL, Pages 273-277						
Examiner /Matthew Song/				Date Considered 08/09/2006 9/27/2006				
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								